

1N4150 THRU 1N4448

HIGH SPEED SWITCHING DIODES

VOLTAGE: 50-100V

CURRENT: 0.15 to 0.2 A

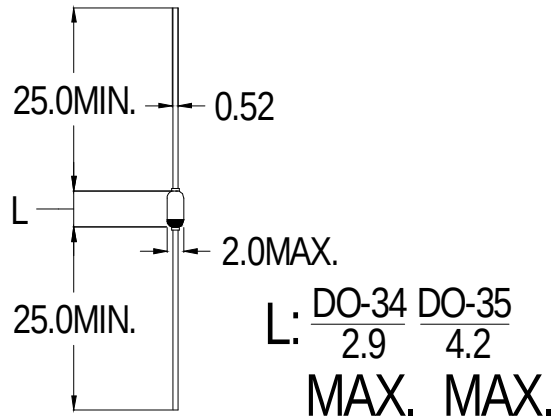
FEATURES

- Silicon epitaxial planar diodes
- Low power loss, high efficiency
- Low leakage
- Low forward voltage
- High speed switching
- High current capability
- High reliability

MECHANICAL DATA

- **Case:** Glass sealed case
- **Lead:** MIL-STD- 202E, Method 208 guaranteed
- **Polarity:** Color band denotes cathode end
- **Mounting position:** Any
- **Weight:** 0.13 gram

DO-35



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

	SYMBOL	1N4150	1N4151	1N4448	units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	75	100	V
Maximum power dissipation $t_{amb}=25^{\circ}C$	P_{tot}	500	500	500	mW
Maximum Forward Voltage	V_F	1.0/200	1.0/50	1.0/100	V/mA
Maximum reverse current	I_R	100/50	50/50	5000/75	nA/V
Maximum reverse recovery time	t_{rr}	4.0	2.0	4.0	nS
Maximum junction capacitance	C_J	4.0			pF

Notes: 1-1N914A, 1N914B is same as 1N914, except different forward voltage|:

1N914A-1.0/20 V/mA

1N914B-1.0/100 V/mA

2. Suffix "M" stands for "DO-34" package. (e.g.: 1N4148M)